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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

FAIRCHILD SEMICONDUCTOR®

2014 年 2 月

FCU900N60Z

N 沟道 SuperFET® II MOSFET

600 V、 4.5 A、 900 mΩ

特性

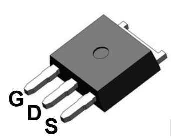
- 675 V @ T_J = 150°C
- 典型值 $R_{DS(on)}$ = 820 mΩ
- 超低栅极电荷 （典型值 Q_g = 13 nC)
- 低有效输出电容 （典型值 $C_{oss(eff.)}$= 48.6 pF)
- 100% 经过雪崩测试
- 提高静电放电保护能力
- 符合 RoHS 标准

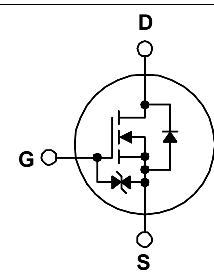
应用

- LCD / LED / PDP 电视和显示器灯光
- 光伏逆变器
- 充电器

说明

SuperFET® II MOSFET 是飞兆半导体新一代利用电荷平衡技术实现出色低导通电阻和更低栅极电荷性能的高压超级结 (SJ) MOSFET 系列产品。这项技术专用于最小化导通损耗并提供卓越的开关性能、 dv/dt 额定值和更高雪崩能量。因此， SuperFET MOSFET 非常适合开关电源应用，如功率因数校正 (PFC)、服务器 / 电信电源、平板电视电源、 ATX 电源及工业电源应用。





绝对最大额定值 T_C = 25°C 除非另有说明。

符号	参数		FCU900N60Z	单位
V_{DSS}	漏极－源极电压		600	V
V_{GSS}	栅极－源极电压	- DC	±20	V
		- AC (f > 1 Hz)	±30	
I_D	漏极电流	- 连续 (T_C = 25°C)	4.5	A
		- 连续 (T_C = 100°C)	2.8	
I_{DM}	漏极电流	- 脉冲 （说明 1）	13.5	A
E_{AS}	单脉冲雪崩能量	（说明 2）	47.5	mJ
I_{AR}	雪崩电流	（说明 1）	1	A
E_{AR}	重复雪崩能量	（说明 1）	0.52	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	二极管恢复 dv/dt 峰值	（说明 3）	20	
P_D	功耗	(T_C = 25°C)	52	W
		- 降低至 25°C 以上	0.42	W/°C
T_J, T_{STG}	工作和存储温度范围		-55 至 +150	°C
T_L	用于焊接的最大引线温度，距离外壳 1/8"，持续 5 秒		300	°C

热性能

符号	参数	FCU900N60Z	单位
$R_{\theta JC}$	结至外壳热阻最大值	2.4	°C/W
$R_{\theta JA}$	结至环境热阻最大值	100	

封装标识与定购信息

器件编号	顶标	封装	包装方法	卷尺寸	带宽	数量
FCU900N60Z	FCU900N60Z	IPAK	塑料管	不适用	不适用	70 单元

电气特性 T_C = 25°C 除非另有说明。

符号	参数	测试条件	最小值	典型值	最大值	单位
关断特性						
BV_{DSS}	漏极－源极击穿电压	I_D = 1 mA, V_{GS} = 0 V, T_J = 25°C	625	-	-	V
		I_D = 1 mA, V_{GS} = 0 V, T_J = 150°C	675	-	-	
ΔBV_{DSS} / ΔT_J	击穿电压温度系数	I_D = 1 mA，参考条件为 25°C	-	0.72	-	V/°C
BV_{DS}	漏极 - 源极雪崩击穿电压	V_{GS} = 0 V, I_D = 4.5 A	-	700	-	V
I_{DSS}	零栅极电压漏极电流	V_{DS} = 600 V, V_{GS} = 0 V	-	-	1	μA
		V_{DS} = 600 V, T_C = 125°C	-	-	10	
I_{GSS}	栅极 - 体漏电流	V_{GS} = ±20 V, V_{DS} = 0 V	-	-	±10	μA
导通特性						
$V_{GS(th)}$	栅极阈值电压	V_{GS} = V_{DS}, I_D = 250 μA	2.5	-	3.5	V
$R_{DS(on)}$	漏极至源极静态导通电阻	V_{GS} = 10 V, I_D = 2.3 A	-	0.82	0.90	Ω
g_{FS}	正向跨导	V_{DS} = 20 V, I_D = 2.3 A	-	4.6	-	S
动态特性						
C_{iss}	输入电容	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	-	534	710	pF
C_{oss}	输出电容		-	399	530	pF
C_{rss}	反向传输电容		-	19.7	30	pF
C_{oss}	输出电容	V_{DS} = 380 V, V_{GS} = 0 V, f = 1 MHz	-	11.1	-	pF
$C_{oss(eff.)}$	有效输出电容	V_{DS} = 0 V 至 480 V， V_{GS} = 0 V	-	48.6	-	pF
$Q_{g(tot)}$	10 V 的栅极电荷总量	V_{DS} = 380 V, I_D = 2.3 A, V_{GS} = 10 V （说明 4）	-	13.1	17	nC
Q_{gs}	栅极 - 源极栅极电荷		-	2.2	-	nC
Q_{gd}	栅极 - 漏极 " 米勒 " 电荷		-	4.5	-	nC
ESR	等效串联电阻	f = 1 MHz	-	2.4	-	Ω
开关特性						
$t_{d(on)}$	导通延迟时间	V_{DD} = 380 V, I_D = 2.3 A, V_{GS} = 10 V, R_G = 4.7 Ω （说明 4）	-	10.9	32	ns
t_r	开通上升时间		-	5.3	21	ns
$t_{d(off)}$	关断延迟时间		-	33.6	77	ns
t_f	关断下降时间		-	11.9	34	ns
漏极 - 源极二极管特性						
I_S	漏极 - 源极二极管最大正向连续电流		-	-	4.5	A
I_{SM}	漏极 - 源极二极管最大正向脉冲电流		-	-	13.5	A
V_{SD}	漏极 - 源极二极管正向电压	V_{GS} = 0 V, I_{SD} = 2.3 A	-	-	1.2	V
t_{rr}	反向恢复时间	V_{GS} = 0 V, I_{SD} = 2.3 A, dI_F/dt = 100 A/μs	-	156	-	ns
Q_{rr}	反向恢复电荷		-	1.3	-	μC

注意：

1. 重复额定值：脉冲宽度受限于最大结温。
2. I_{AS} = 1.0 A， V_{DD} = 50 V， R_G = 25 Ω，启动 T_J = 25°C。
3. I_{SD} ≤ 2.3 A， di/dt ≤ 200 A/μs， V_{DD} ≤ BV_{DSS}，启动 T_J = 25°C。
4. 本质上独立于工作温度。

典型性能特征

图 1. 导通区域特性

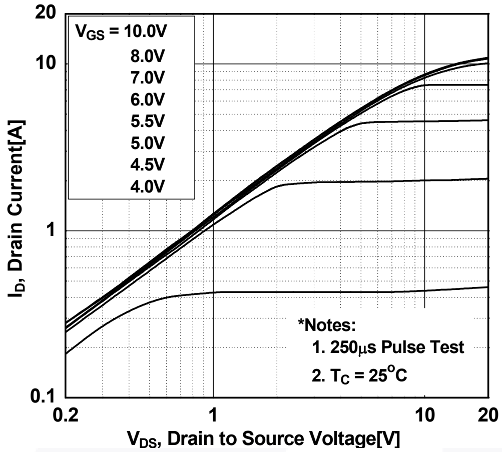


图 2. 传输特性

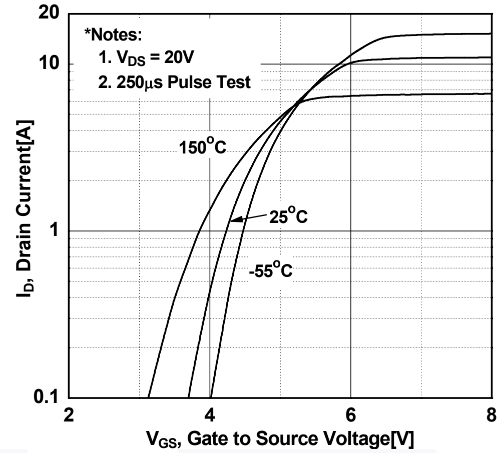


图 3. 导通电阻变化与漏极电流和栅极电压

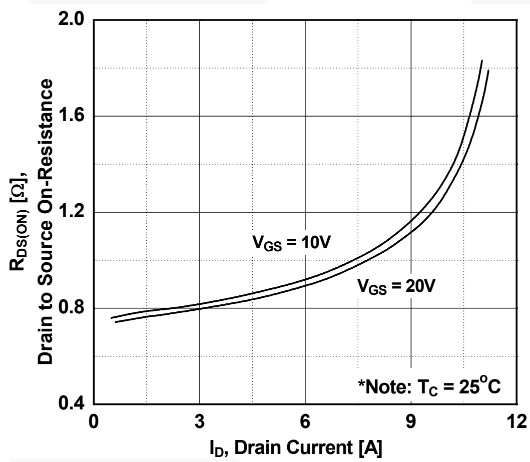


图 4. 体二极管正向电压变化与源极电流和温度

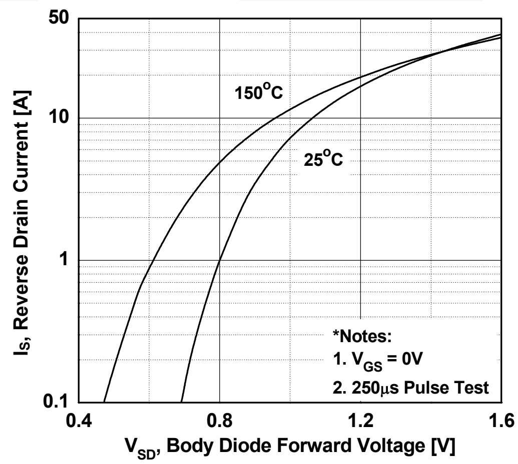


图 5. 电容特性

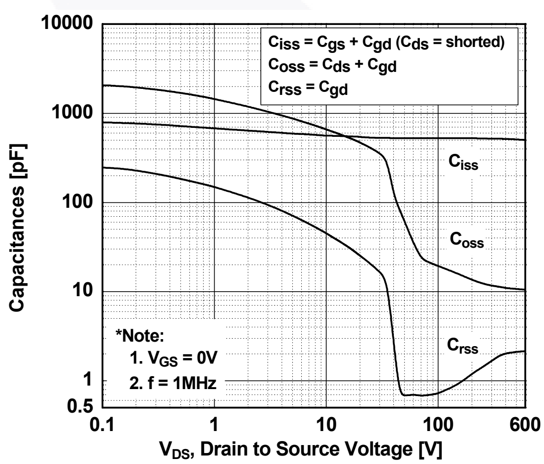
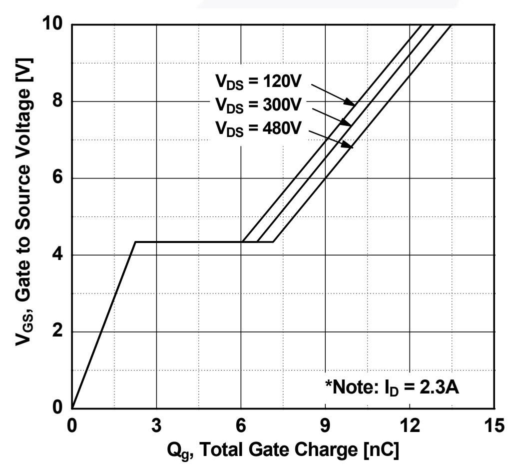


图 6. 栅极电荷特性



典型性能特征（接上页）

图 7. 击穿电压变化与温度

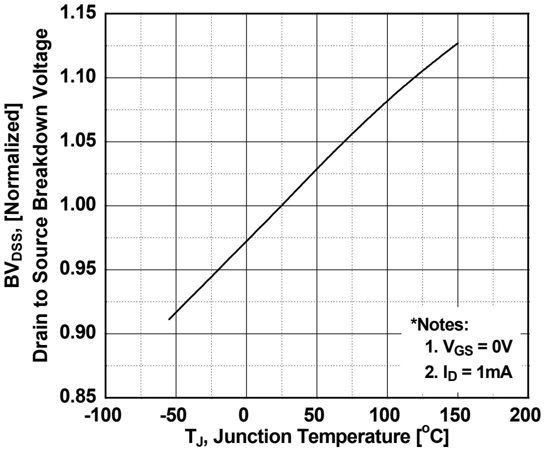


图 8. 导通电阻变化与温度

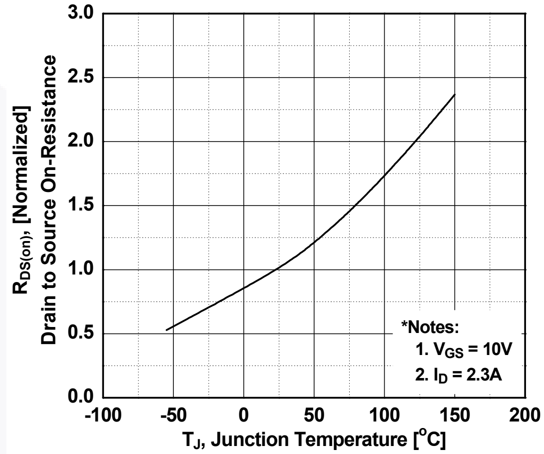


图 9. 最大安全工作区

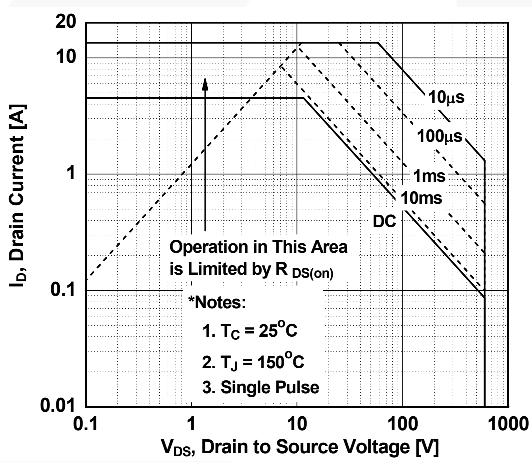


图 10. 最大漏极电流与外壳温度

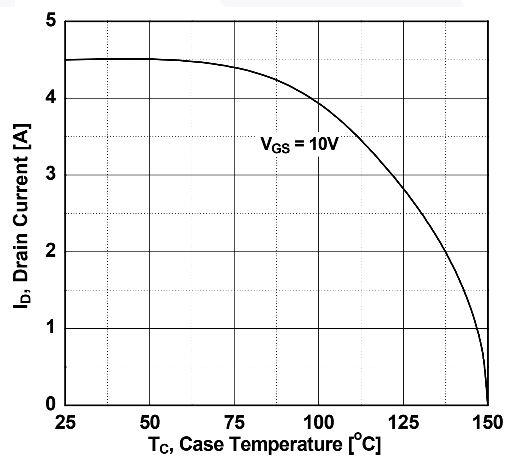
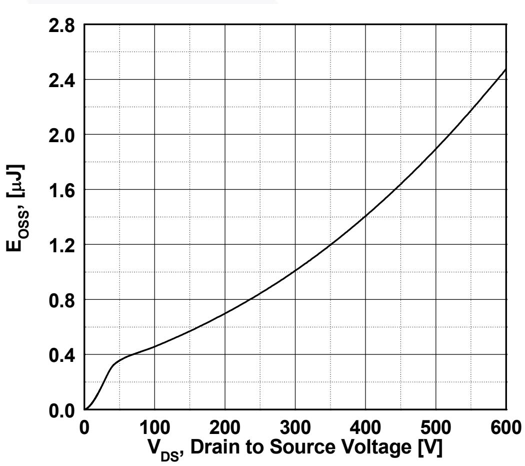
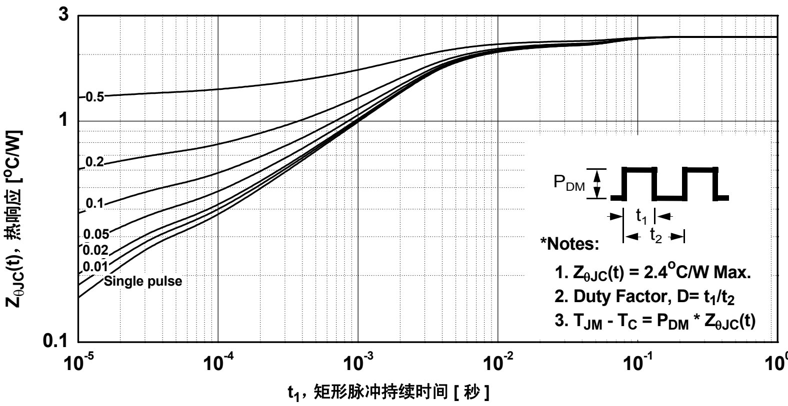


图 11. Eoss 与漏极一源极电压的关系



典型性能特征（接上页）

图 12. 瞬态热响应曲线



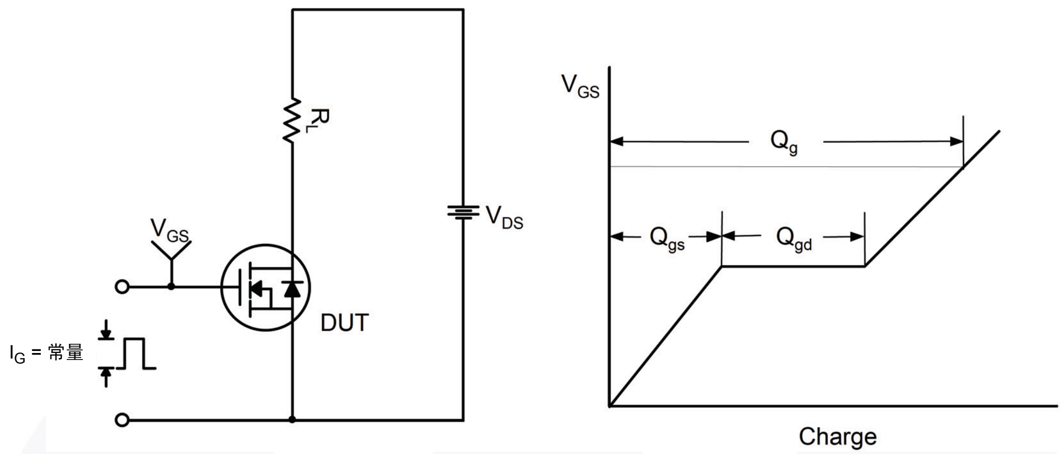


图 13. 栅极电荷测试电路与波形

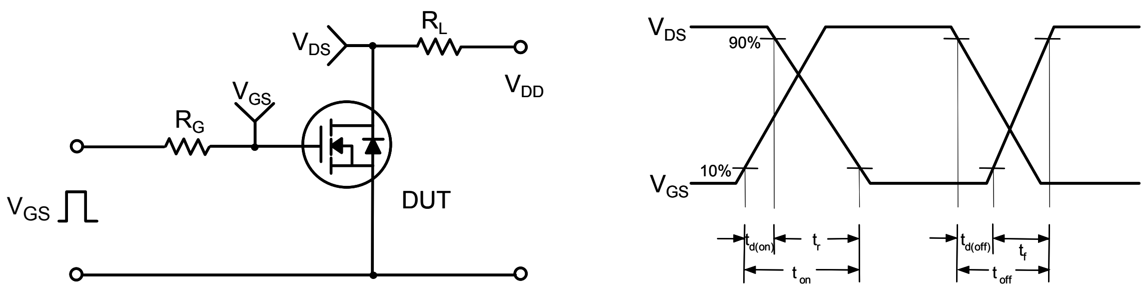


图 14. 阻性开关测试电路与波形

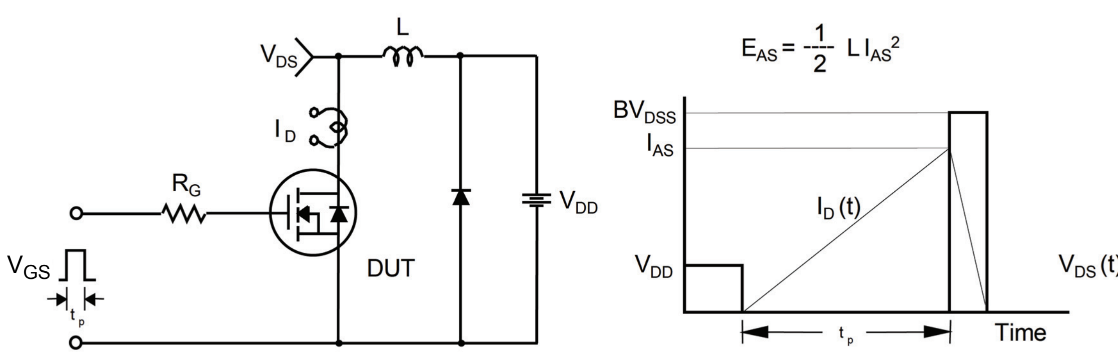


图 15. 非箝位电感开关测试电路与波形

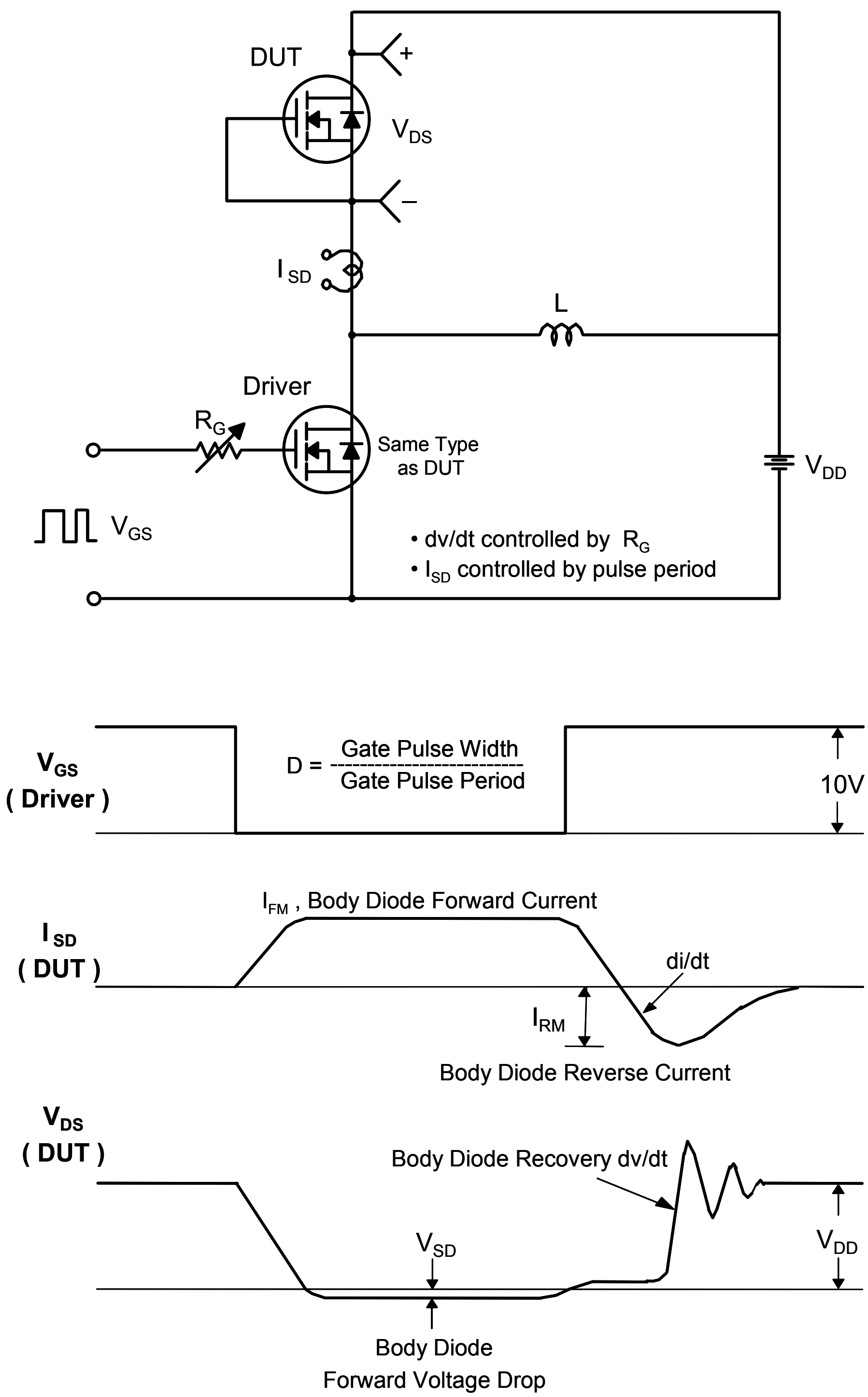
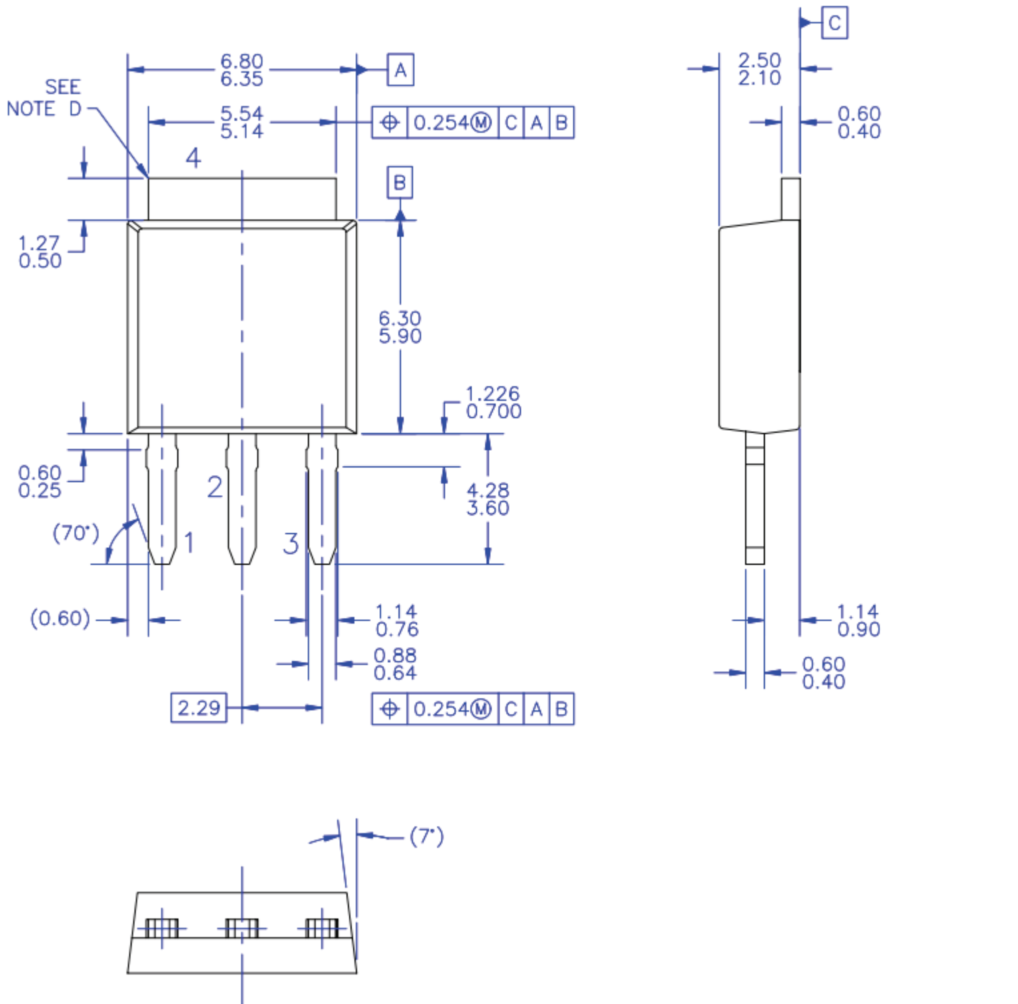


图 16. 二极管恢复 dv/dt 峰值测试电路与波形

机械尺寸



NOTES: UNLESS OTHERWISE SPECIFIED

A) ALL DIMENSIONS ARE IN MILLIMETERS.
B) PACKAGE BODY REFERENCE: JEDEC, TO-251, ISSUE D, VARIATION AA, DATED JUNE 2002.
C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
D) HEAT SINK TOP EDGE COULD BE IN CHAMFERED CORNERS OR EDGE PROTRUSION.
E) DRAWING FILE NAME: TO251B03_3

图 17. TO251 (I-PAK)，模塑， 3 引脚 （短引脚）， FO71

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Datasheet Identification	Product Status	Definition
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I66

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